



FAST CMOS OCTAL D REGISTERS (3-STATE)

IDT54/74FCT574/A/C

FEATURES:

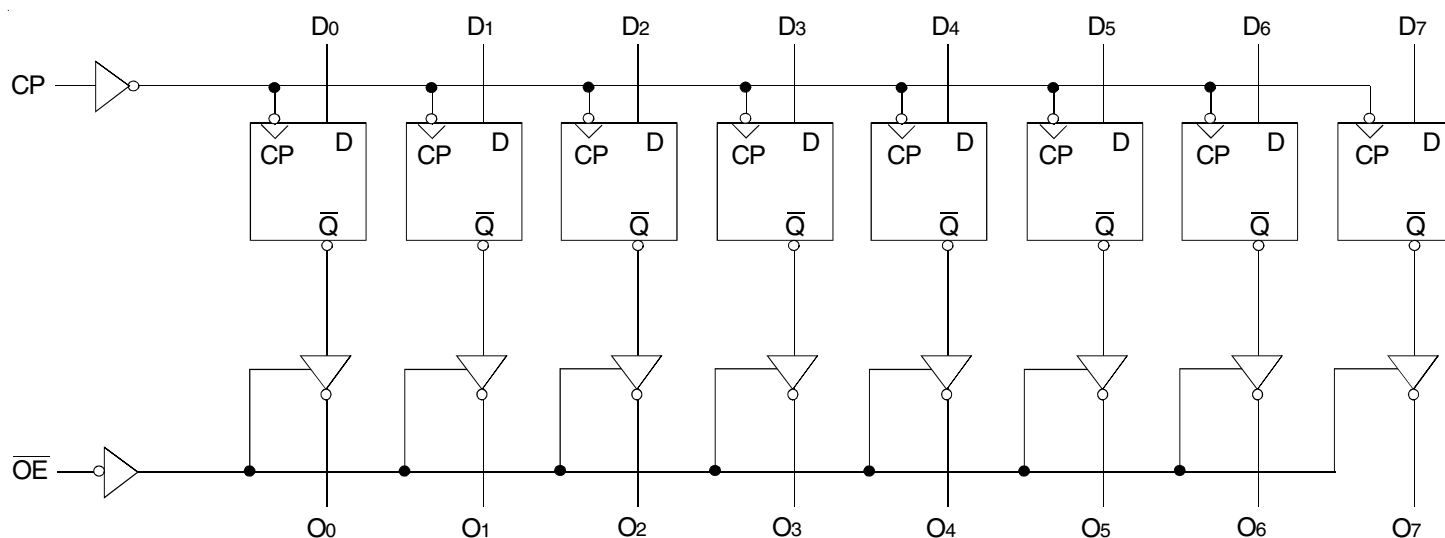
- IDT54FCT574A equivalent to FAST™ speed and drive
- IDT54/74FCT574A up to 30% faster than FAST
- IDT74FCT574C up to 50% faster than FAST
- $I_{OL} = 48\text{mA}$ (commercial) and 32mA (military)
- CMOS power levels (1mW typ. static)
- Edge-triggered master/slave, D-type flip-flops
- Buffered common clock and buffered common 3-state control
- Military product compliant to MIL-STD-883, Class B
- Meets or exceeds JEDEC Standard 18 specifications
- Available in the following packages:
 - Commercial: SOIC
 - Military: CERDIP, LCC

DESCRIPTION:

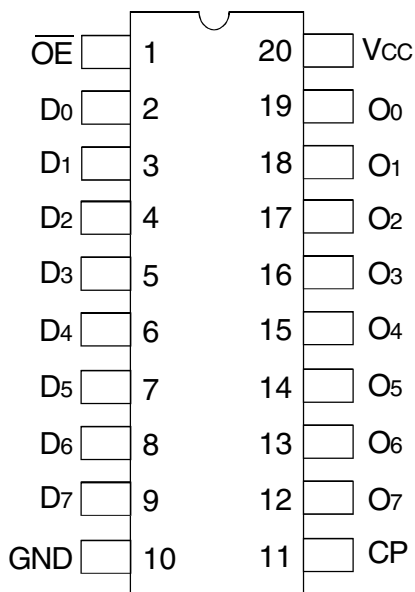
The FCT574 is an 8-bit register built using an advanced dual metal CMOS technology. These registers consist of eight D-type flip-flops with a buffered common clock and buffered 3-state output control. When the output enable (\overline{OE}) is low, the eight outputs are enabled. When the \overline{OE} input is high, the outputs are in the high-impedance state.

Input data meeting the set-up and hold time requirements of the D inputs is transferred to the O outputs on the low-to-high transition of the clock input. The FCT574 has non-inverting outputs with respect to the data at the D inputs.

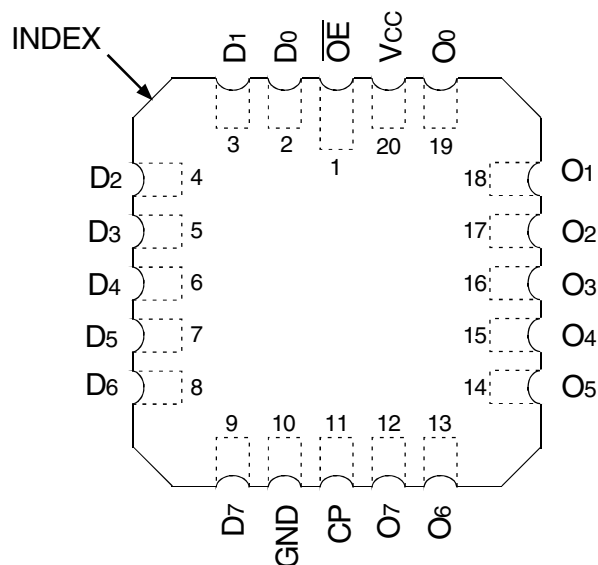
FUNCTIONAL BLOCK DIAGRAM



PIN CONFIGURATION



CERDIP/ SOIC
TOP VIEW



LCC
TOP VIEW

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Rating	Commercial	Military	Unit
V _{TERM} ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7	-0.5 to +7	V
V _{TERM} ⁽³⁾	Terminal Voltage with Respect to GND	-0.5 to V _{CC}	-0.5 to V _{CC}	V
T _A	Operating Temperature	0 to +70	-55 to +125	°C
T _{BIAS}	Temperature under BIAS	-55 to +125	-65 to +135	°C
T _{STG}	Storage Temperature	-55 to +125	-65 to +150	°C
P _T	Power Dissipation	0.5	0.5	W
I _{OUT}	DC Output Current	120	120	mA

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability. No terminal voltage may exceed V_{CC} by +0.5V unless otherwise noted.
- Input and V_{CC} terminals only.
- Output and I/O terminals only.

CAPACITANCE (T_A = +25°C, F = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Typ.	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 0V	6	10	pF
C _{OUT}	Output Capacitance	V _{OUT} = 0V	8	12	pF

NOTE:

- This parameter is measured at characterization but not tested.

PIN DESCRIPTION

Pin Names	Description
D _x	D flip-flop data inputs
CP	Clock Pulse for the register. Enters data on LOW-to-HIGH transition.
O _x	3-State Outputs (TRUE)
\overline{OE}	Active LOW 3-State Output Enable Input

FUNCTION TABLE⁽¹⁾

Function	Inputs			Outputs	Internal
	\overline{OE}	CP	D _x	O _x	\overline{Ox}
High-Z	H	L	X	Z	NC
	H	H	X	Z	NC
Load Register	L	↑	L	L	H
	L	↑	H	H	L
	H	↑	L	Z	H
	H	↑	H	Z	L

NOTE:

- H = HIGH Voltage Level
X = Don't Care
L = LOW Voltage Level
Z = High Impedance
NC = No Change
↑ = LOW-to-HIGH transition

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified: $V_{LC} = 0.2V$; $V_{HC} = V_{CC} - 0.2V$

Commercial: $T_A = 0^\circ C$ to $+70^\circ C$, $V_{CC} = 5.0V \pm 5\%$, Military: $T_A = -55^\circ C$ to $+125^\circ C$, $V_{CC} = 5.0V \pm 10\%$

Symbol	Parameter	Test Conditions ⁽¹⁾		Min.	Typ. ⁽²⁾	Max.	Unit
V _{IH}	Input HIGH Level	Guaranteed Logic HIGH Level		2	—	—	V
V _{IL}	Input LOW Level	Guaranteed Logic LOW Level		—	—	0.8	V
I _{IH}	Input HIGH Current	V _{CC} = Max.	V _I = V _{CC}	—	—	5	μA
I _{IL}	Input LOW Current		V _I = 2.7V	—	—	5 ⁽⁴⁾	
			V _I = 0.5V	—	—	-5 ⁽⁴⁾	
			V _I = GND	—	—	-5	
I _{OZH}	Off State (High Impedance) Output Current	V _{CC} = Max.	V _O = V _{CC}	—	—	10	μA
I _{OZL}			V _O = 2.7V	—	—	10 ⁽⁴⁾	
			V _O = 0.5V	—	—	-10 ⁽⁴⁾	
			V _O = GND	—	—	-10	
V _{IK}	Clamp Diode Voltage	V _{CC} = Min., I _{IN} = -18mA		—	-0.7	-1.2	V
I _{OS}	Short Circuit Current	V _{CC} = Max., V _O = GND ⁽³⁾		-60	-120	—	mA
V _{OH}	Output HIGH Voltage	V _{CC} = 3V, V _{IN} = V _{LC} or V _{HC} , I _{OH} = -32μA		V _{HC}	V _{CC}	—	V
		V _{CC} = Min V _{IN} = V _{IH} or V _{IL}	I _{OH} = -300μA	V _{HC}	V _{CC}	—	
			I _{OH} = -12mA MIL	2.4	4.3	—	
			I _{OH} = -15mA COM'L	2.4	4.3	—	
V _{OL}	Output LOW Voltage	V _{CC} = 3V, V _{IN} = V _{LC} or V _{HC} , I _{OL} = 300μA		—	GND	V _{LC}	V
		V _{CC} = Min V _{IN} = V _{IH} or V _{IL}	I _{OL} = 300μA	—	GND	V _{LC} ⁽⁴⁾	
			I _{OL} = 32mA MIL	—	0.3	0.5	
			I _{OL} = 48mA COM'L	—	0.3	0.5	

NOTES:

1. For conditions shown as Min. or Max., use appropriate value specified under Electrical Characteristics for the applicable device type.
2. Typical values are at $V_{CC} = 5.0V$, $+25^\circ C$ ambient and maximum loading.
3. Not more than one output should be tested at one time. Duration of the test should not exceed one second.
4. This parameter is guaranteed but not tested.

POWER SUPPLY CHARACTERISTICS

$V_{LC} = 0.2V$; $V_{HC} = V_{CC} - 0.2V$

Symbol	Parameter	Test Conditions ⁽¹⁾		Min.	Typ. ⁽²⁾	Max.	Unit
I _{CC}	Quiescent Power Supply Current	V _{CC} = Max. V _{IN} ≥ V _{HC} ; V _{IN} ≤ V _{LC}		—	0.2	1.5	mA
ΔI _{CC}	Quiescent Power Supply Current TTL Inputs HIGH	V _{CC} = Max. V _{IN} = 3.4V ⁽³⁾		—	0.5	2	mA
I _{CCD}	Dynamic Power Supply Current ⁽⁴⁾	V _{CC} = Max. Outputs Open $\overline{OE} = GND$ One Input Toggling 50% Duty Cycle	V _{IN} ≥ V _{HC} V _{IN} ≤ V _{LC}	—	0.15	0.25	mA/ MHz
I _C	Total Power Supply Current ⁽⁶⁾	V _{CC} = Max. Outputs Open f _{CP} = 10MHz 50% Duty Cycle $\overline{OE} = GND$ fi = 5MHz One Bit Toggling	V _{IN} ≥ V _{HC} V _{IN} ≤ V _{LC} (FCT)	—	1.7	4	mA
			V _{IN} = 3.4V V _{IN} = GND	—	2.2	6	
		V _{CC} = Max. Outputs Open f _{CP} = 10MHz 50% Duty Cycle $\overline{OE} = GND$ fi = 2.5MHz Eight Bits Toggling	V _{IN} ≥ V _{HC} V _{IN} ≤ V _{LC} (FCT)	—	4	7.8 ⁽⁵⁾	
			V _{IN} = 3.4V V _{IN} = GND	—	6.2	16.8 ⁽⁵⁾	

NOTES:

1. For conditions shown as Min. or Max., use appropriate value specified under Electrical Characteristics for the applicable device type.

2. Typical values are at V_{CC} = 5.0V, +25°C ambient.

3. Per TTL driven input (V_{IN} = 3.4V). All other inputs at V_{CC} or GND.

4. This parameter is not directly testable, but is derived for use in Total Power Supply Calculations.

5. Values for these conditions are examples of ΔI_{CC} formula. These limits are guaranteed but not tested.

6. I_C = I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}

I_C = I_{CC} + ΔI_{CC} D_HN_T + I_{CCD} (f_{CP}/2 + fiNi)

I_{CC} = Quiescent Current

ΔI_{CC} = Power Supply Current for a TTL High Input (V_{IN} = 3.4V)

D_H = Duty Cycle for TTL Inputs High

N_T = Number of TTL Inputs at D_H

I_{CCD} = Dynamic Current caused by an Input Transition Pair (HLH or LHL)

f_{CP} = Clock Frequency for register devices (zero for non-register devices)

fi = Input Frequency

Ni = Number of Inputs at fi

All currents are in milliamps and all frequencies are in megahertz.

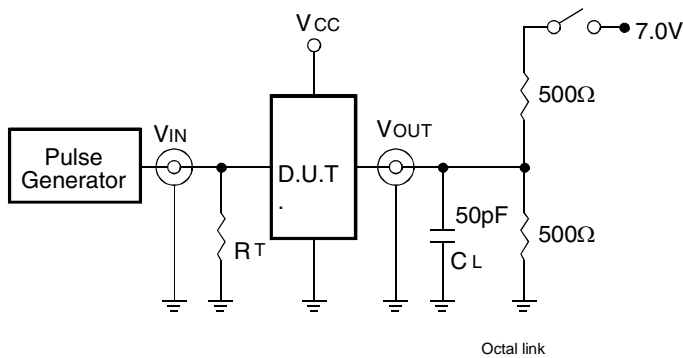
SWITCHING CHARACTERISTICS OVER OPERATING RANGE

Symbol	Parameter	Condition ⁽¹⁾	54FCT574		54/74FCT574A				74FCT574C		Unit
			Mil.		Com'l.		Mil.		Com'l.		
			Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	
tPLH	Propagation Delay	CL = 50pF RL = 500Ω	2	11	2	6.5	2	7.2	2	5.2	ns
tPHL	CP to Qx										
tPZH	Output Enable Time		1.5	14	1.5	6.5	1.5	7.5	1.5	5.5	ns
tPZL											
tPHZ	Output Disable Time		1.5	8	1.5	5.5	1.5	6.5	1.5	5	ns
tPLZ											
tSU	Set-up Time HIGH or LOW Dx to CP		2	—	2	—	2	—	2	—	ns
tH	Hold Time HIGH or LOW Dx to CP	1.5	—	1.5	—	1.5	—	1.5	—	ns	
tw	CP Pulse Width HIGH or LOW ⁽³⁾	7	—	5	—	6	—	5	—	ns	

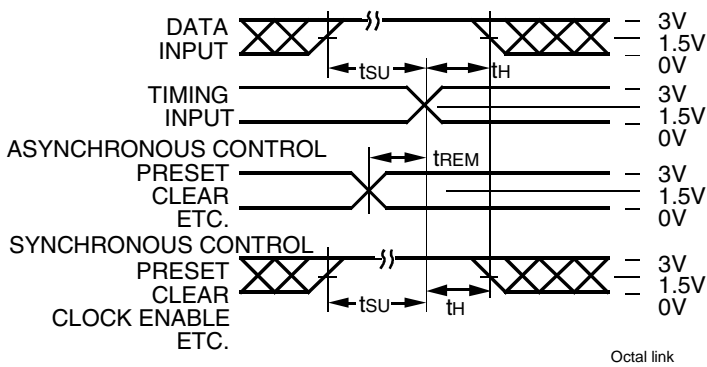
NOTES:

1. See test circuit and waveforms.
2. Minimum limits are guaranteed but not tested on Propagation Delays.
3. This parameter is guaranteed but not tested.

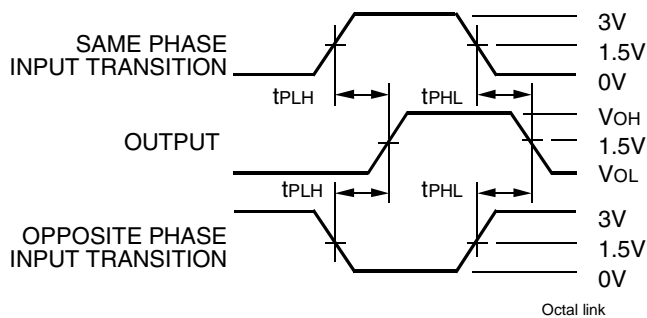
TEST CIRCUITS AND WAVEFORMS



Test Circuits for All Outputs



Set-Up, Hold, and Release Times



Propagation Delay

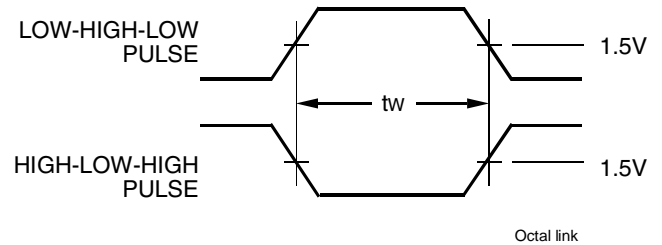
SWITCH POSITION

Test	Switch
Open Drain Disable Low Enable Low	Closed
All Other Tests	Open

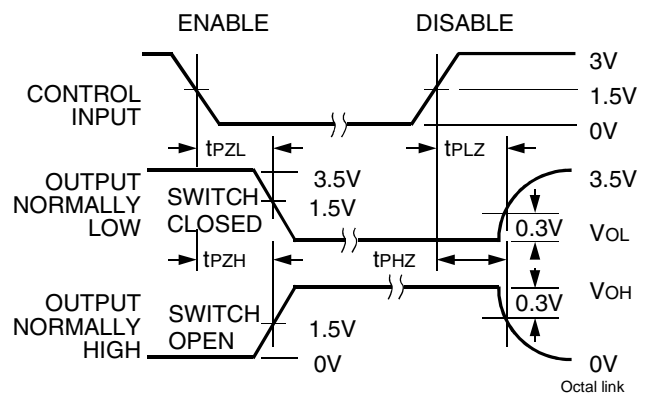
DEFINITIONS:

CL = Load capacitance: includes jig and probe capacitance.

RT = Termination resistance: should be equal to ZOUT of the Pulse Generator.



Pulse Width



Enable and Disable Times

NOTES:

- Diagram shown for input Control Enable-LOW and input Control Disable-HIGH.
- Pulse Generator for All Pulses: Rate $\leq 1.0\text{MHz}$; $Z_o \leq 50\Omega$; $t_r \leq 2.5\text{ns}$; $t_f \leq 2.5\text{ns}$.

ORDERING INFORMATION

IDT	XX	FCT	XXXX	XX	X	
	Temp. Range		Device Type	Package	Process	
					Blank B	Commercial MIL-STD-883, Class B
					SO	<u>Commercial Options</u> Small Outline IC
					D L	<u>Military Options</u> CERDIP Leadless Chip Carrier
					574 574A 574C	Fast CMOS Octal D Register (3-State)
					54 74	– 55°C to +125°C 0°C to +70°C



CORPORATE HEADQUARTERS
2975 Stender Way
Santa Clara, CA 95054

for SALES:
800-345-7015 or 408-727-6116
fax: 408-492-8674
www.idt.com

for Tech Support:
logichelp@idt.com
(408) 654-6459